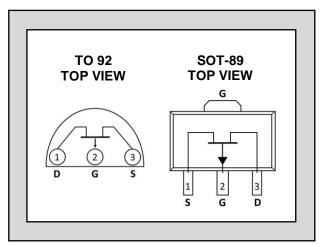


Twenty-Five Years Of Quality Through Innovation

LSJ74, SST74

ULTRA LOW NOISE SINGLE P-CHANNEL JFET

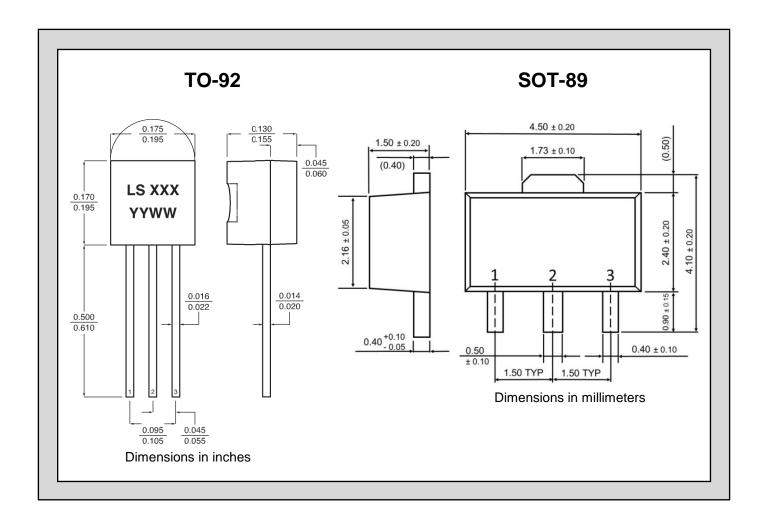
FEATURES					
ULTRA LOW NOISE (f = 1kHz)	$e_n = 0.9 \text{nV}/\sqrt{\text{Hz}}$				
HIGH GAIN	$G_{fs} = 22mS (typ)$				
HIGH INPUT IMPEDANCE	$I_G = 1.0 \text{nA}$				
LOW CAPACITANCE	C _{RSS} = 32pF				
IMPROVED SECOND SOURCE REPLACEMENT FOR 2SJ74					
ABSOLUTE MAXIMUM RATINGS¹ @ 25 °C (unless otherwise stated)					
Maximum Temperatures					
Storage Temperature	-55 to +150°C				
Junction Operating Temperature	-55 to +135°C				
Maximum Power Dissipation					
Continuous Power Dissipation	400mW				
Maximum Currents					
Gate Forward Current	$I_{G(F)} = -10mA$				
Maximum Voltages					
Gate to Drain Voltage	$V_{GDS} = 25V$				
Gate to Source Voltage	V _{GSS} = 25V				



^{*} For equivalent N-Channel, see LSK170 family.

ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC		MIN	TYP	MAX	UNITS	CONDITIONS		
BV _{GDS}	Gate to Drain Breakdown Voltage		25			V	$V_{DS} = 0V, I_G = 100 \mu A$		
V _{GS(OFF)}	Gate to Source Pinch-off Voltage		0.15		2		$V_{DS} = -10V, I_{D} = -0.1 \mu A$		
Ibss	Drain to Source Saturation Current ²	LSJ74A	-2.6		-6.5	mA	mA V _{DG} = -10V, V _{GS} = 0V		
		LSJ74B	-6		-12				
		LSJ74C	-10		-20				
		LSJ74D	-17		-30				
lg	Gate Operating Current			50		pА	$V_{DG} = -10V, I_{D} = -1mA$		
Igss	Gate to Source Leakage Current				1	nA	$V_{GS} = 25V$, $V_{DS} = 0V$		
G _{fss}	Full Conductance Transconductance		8	22		mS	$V_{DG} = -10V$, $V_{GS} = 0V$, $f = 1kHz$		
	Noise Voltage		Naisa Valtaga			0.9	1.9	nV/√Hz	$V_{DS} = -10V$, $I_D = -2mA$, $f = 1kHz$, $NBW = 1Hz$
e n				2.5	4	IIV/ VIIZ	$V_{DS} = -10V$, $I_{D} = -2mA$, $f = 10kHz$, $NBW = 1Hz$		
C _{ISS}	Common Source Input Capacitance			105	·	pF	$V_{DS} = -10V$, $V_{GS} = 0V$, $f = 1MHz$		
Crss	Common Source Reverse Transfer Cap.			32			$V_{DS} = -10V, I_D = 0A, f = 1MHz$		



NOTES:

- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- 2. Pulse test: PW \leq 300 μ S, Duty Cycle \leq 3%.
- 3. All MIN/TYP/MAX Limits are absolute values. Negative signs indicate negative electrical polarity only.

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